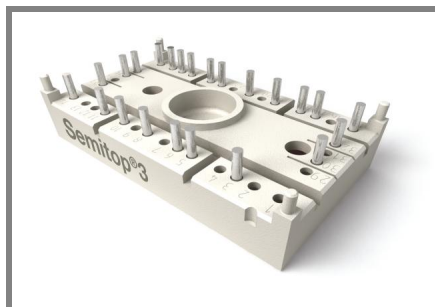


SK80GB125T



SEMITOP® 3

IGBT Module

SK80GB125T

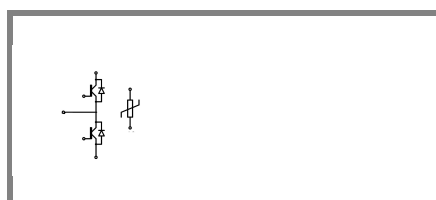
Preliminary Data

Features

- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonding Aluminium Nitride ceramic (DBC)
- High short circuit capability
- Low tail current with low temperature dependence

Typical Applications

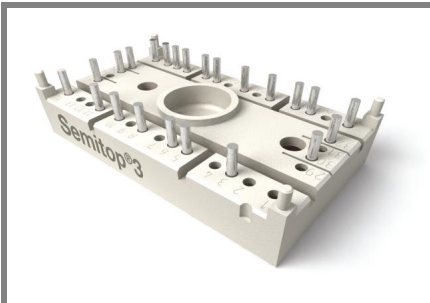
- Switching (not for linear use)
- Inverter
- Switched mode power supplies
- UPS



GB - T

Absolute Maximum Ratings		$T_s = 25\text{ °C}$, unless otherwise specified		
Symbol	Conditions	Values		Units
IGBT				
V_{CES}	$T_j = 25\text{ °C}$	1200		V
I_C	$T_j = 125\text{ °C}$	$T_s = 25\text{ °C}$	85	A
		$T_s = 80\text{ °C}$	55	A
I_{CRM}	$I_{CRM} = 2 \times I_{Cnom}$	150		A
V_{GES}		± 20		V
t_{psc}	$V_{CC} = 300\text{ V}$; $V_{GE} \leq 20\text{ V}$; $T_j = 125\text{ °C}$ $V_{CES} < 600\text{ V}$	10		µs
Inverse Diode				
I_F	$T_j = 150\text{ °C}$	$T_s = 25\text{ °C}$	90	A
		$T_s = 80\text{ °C}$	60	A
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$			A
I_{FSM}	$t_p = 10\text{ ms}$; half sine wave $T_j = 150\text{ °C}$	550		A
Module				
$I_{t(RMS)}$				A
T_{vj}		-40 ... +150		°C
T_{stg}		-40 ... +125		°C
V_{isol}	AC, 1 min.	2500		V

Characteristics		$T_s = 25\text{ °C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 3\text{ mA}$	4,5	5,5	6,5	V
I_{CES}	$V_{GE} = 0\text{ V}$, $V_{CE} = V_{CES}$ $T_j = 25\text{ °C}$			0,01	mA
I_{GES}	$V_{CE} = 0\text{ V}$, $V_{GE} = 20\text{ V}$ $T_j = 25\text{ °C}$			480	nA
V_{CE0}		$T_j = 25\text{ °C}$	1,4	1,9	V
		$T_j = 125\text{ °C}$	1,7	2,2	V
r_{CE}	$V_{GE} = 15\text{ V}$	$T_j = 25\text{ °C}$	18,6		mΩ
		$T_j = 125\text{ °C}$	20		mΩ
$V_{CE(sat)}$	$I_{Cnom} = 75\text{ A}$, $V_{GE} = 15\text{ V}$	$T_j = 25\text{ °C}_{chiplev.}$	3,2	3,3	V
		$T_j = 125\text{ °C}_{chiplev.}$	3,85	3,7	V
C_{ies}	$V_{CE} = 25$, $V_{GE} = 0\text{ V}$ $f = 1\text{ MHz}$			5,1	nF
C_{oes}				0,72	nF
C_{res}				0,38	nF
$t_{d(on)}$	$R_{Gon} = 8,2\ \Omega$	$V_{CC} = 600\text{ V}$ $I_{Cnom} = 80\text{ A}$	180		ns
t_r			110		ns
E_{on}	$R_{Goff} = 8,2\ \Omega$	$T_j = 125\text{ °C}$ $V_{GE} = \pm 15\text{ V}$	9,9		mJ
$t_{d(off)}$			358		ns
t_f			26		ns
E_{off}			5		mJ
$R_{th(j-s)}$	per IGBT			0,32	K/W



SEMITOP® 3

IGBT Module

SK80GB125T

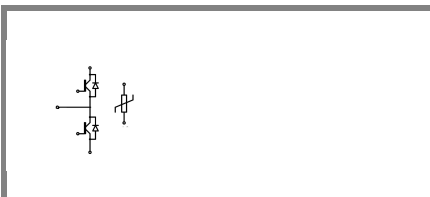
Preliminary Data

Features

- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonding Aluminium Nitride ceramic (DBC)
- High short circuit capability
- Low tail current with low temperature dependence

Typical Applications

- Switching (not for linear use)
- Inverter
- Switched mode power supplies
- UPS



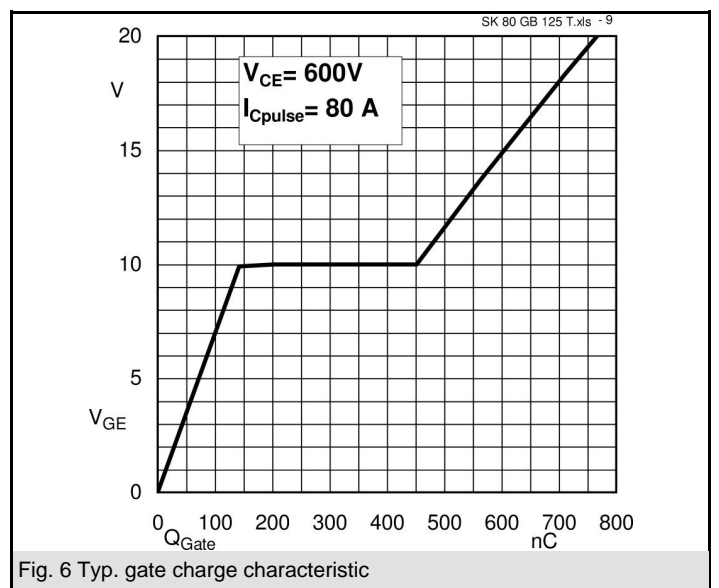
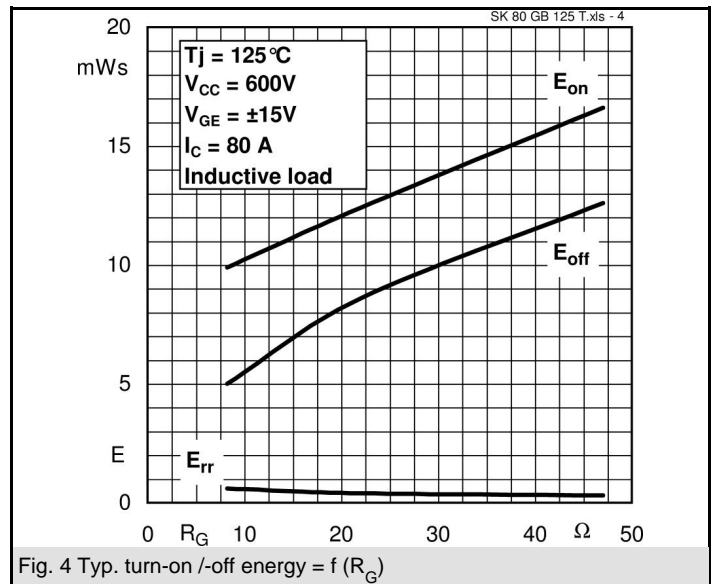
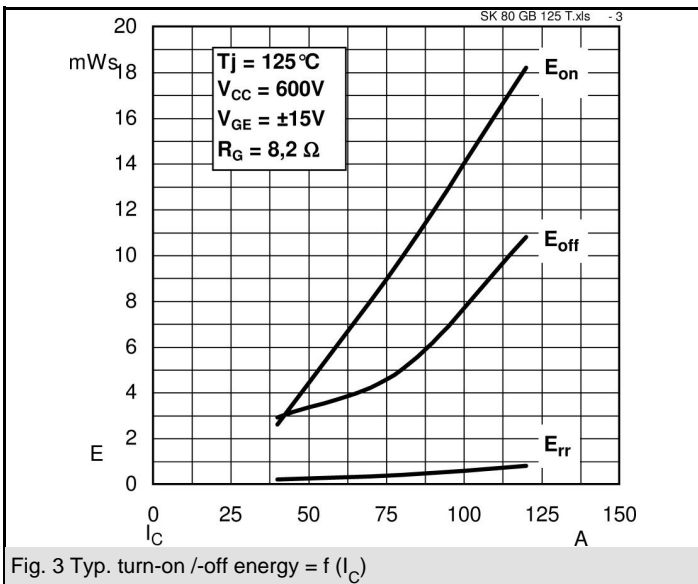
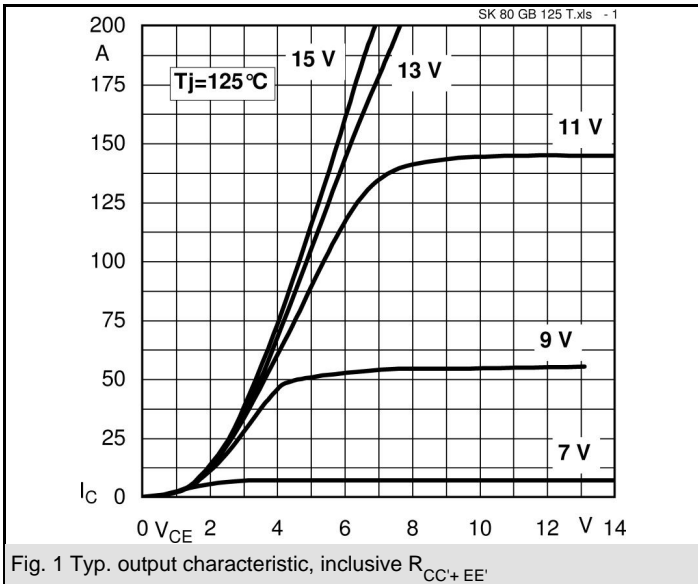
GB - T

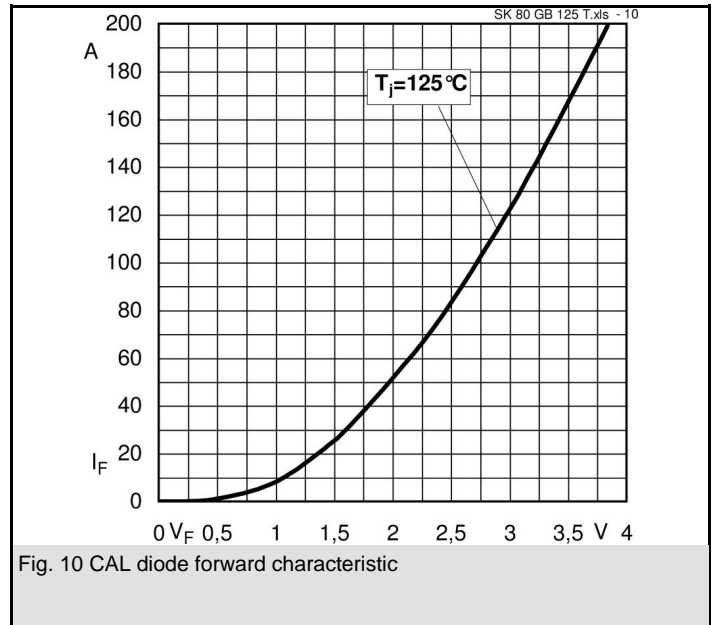
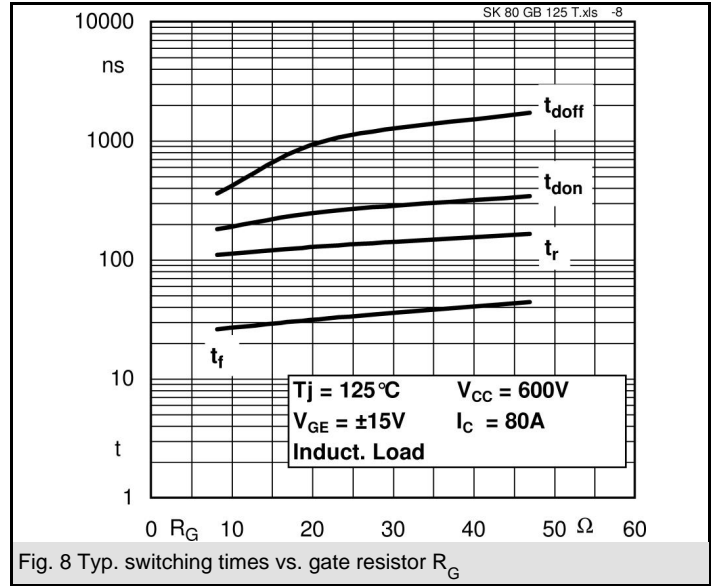
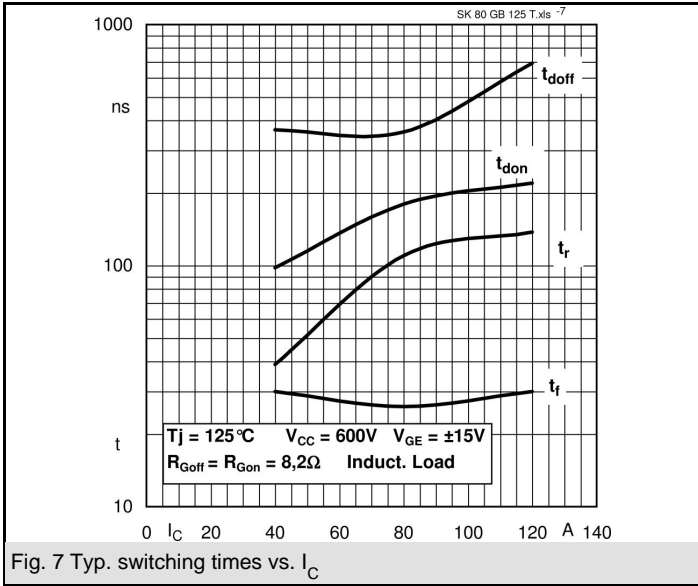
Characteristics

Symbol	Conditions	min.	typ.	max.	Units
Inverse Diode					
$V_F = V_{EC}$	$I_{Fnom} = 55 \text{ A}; V_{GE} = 0 \text{ V}$		2		V
			1,8		V
V_{F0}			1,2		V
r_F			11		mΩ
I_{RRM}	$I_{Fnom} = 50 \text{ A}$		40		A
Q_{rr}	$di/dt = -800 \text{ A}/\mu\text{s}$		8		μC
E_{rr}	$V_{CC} = 600\text{V}$		1		mJ
$R_{th(j-s)D}$	per diode			0,65	K/W
M_s	to heat sink	2,25		2,5	Nm
w			30		g
Temperature sensor					
R_{100}	$T_s = 100^\circ\text{C} (R_{25} = 5\text{k}\Omega)$		493±5%		Ω

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.

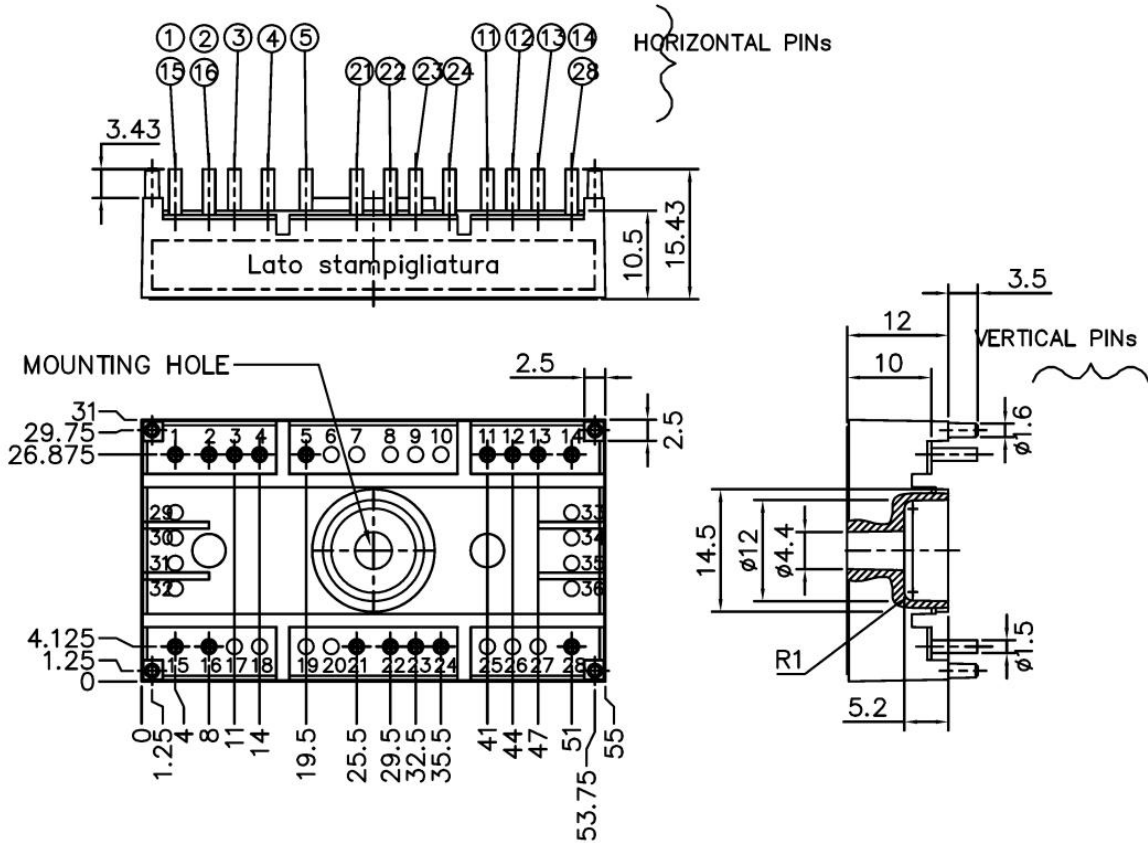




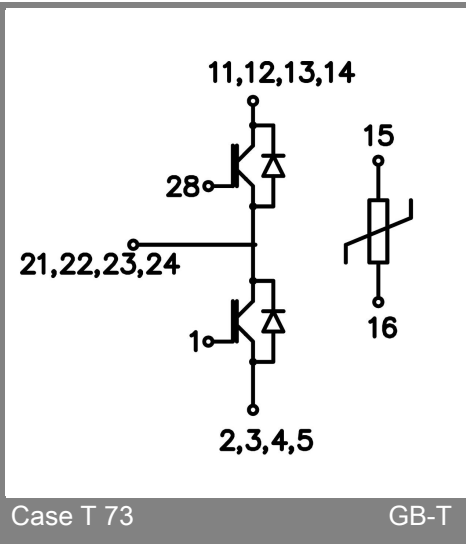
SK80GB125T

UL Recognized
File no. E 63 532

Dimensions in mm



Case T73 (Suggested hole diameter, in the PCB, for solder pins and plastic mounting pins: 2mm)



Case T 73

GB-T